AMENDMENTS TO THE SPECIFICATION

In the Specification

Please replace paragraph [0039] beginning on page 11 with the following amended paragraph:

[0039] Next, as illustrated in Figure 10, the wafer 32 may be placed back onto the wafer chuck 74 with the dispenser head 76 located above. A smoothing solvent 88 may be dispensed from the dispenser head 76 and may cover the entire upper surface 38 of the wafer 32, exposing the wafer 32 to a smoothing medium. Accordingly, the smoothing medium may include a solvent. The smoothing solvent 88 may be a solvent such as ethyl lactate, in which the polymeric layer 28 is only partially, or sparingly, soluble. A puddle of the smoothing solvent 88 may be allowed to stand on the wafer for between 5 and 20 minutes depending on the solvent used, the thickness of the polymeric layer 28, and the degree of smoothing desired. Because the polymer is far less soluble in the smoothing solvent 88, the polymeric layer 28 does not completely dissolve but only partially absorbs some of the smoothing solvent 88. The puddle may have a maximum depth of approximately 2 mm. The polymeric layer 28 does not completely dissolve in the smoothing solvent 88 but experiences a slight swelling as some of the smoothing solvent penetrates the layer 28. Accordingly, a film on a semiconductor substrate may be exposed to a smoothing medium to reduce a height of a plurality of roughness formations on a surface thereof.

Please replace paragraph [0040] beginning on page 11 with the following amended paragraph:

[0040] Once the degree of smoothing has been obtained, the film may be removed from the smoothing medium. [[the]] The wafer 32 may be then spun by the wafer chuck 74 to

remove the standing puddle of smoothing solvent 88, and then baked again. This bake may include, for example, heating the wafer 32 to a temperature of 110 degrees Celsius for two minutes to remove any residual smoothing solvent 88.